

Silicon NPN Power Transistors

BD230

DESCRIPTION

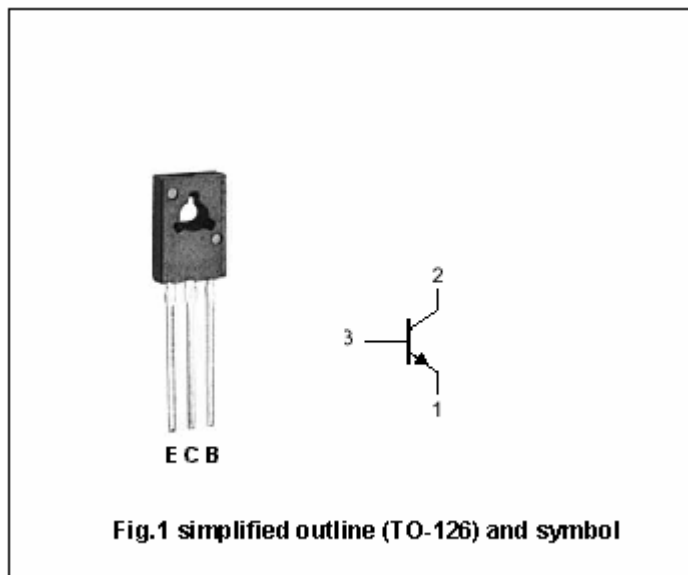
- With TO-126 package
- Complement to type BD231
- High current (Max:1.5A)
- Low voltage (Max: 80V)

APPLICATIONS

- Drive stage in TV circuits

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		1.5	A
I _{CM}	Collector current-Peak		3	A
I _{BM}	Base current-Peak		1	A
P _D	Total power dissipation	T _{mb} ≤62℃	12.5	W
		T _C =25℃	10	
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-65~150	℃
T _{amb}	Operating ambient temperature		-65~150	℃

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.1A			0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A; I _B =0.1A			1.2	V
V _{BE}	Base-emitter on voltage	I _C =1A; V _{CE} =2V			1.3	V
I _{CBO}	Collector cut-off current	V _{CB} =30V; I _E =0			0.1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	μA
h _{FE-1}	DC current gain	I _C =5mA; V _{CE} =2V	40			
h _{FE-2}	DC current gain	I _C =150mA; V _{CE} =2V	40		250	
h _{FE-3}	DC current gain	I _C =1A; V _{CE} =2V	25			
f _T	Transition frequency	I _C =50mA; V _{CE} =5V		125		MHz

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PACKAGE OUTLINE

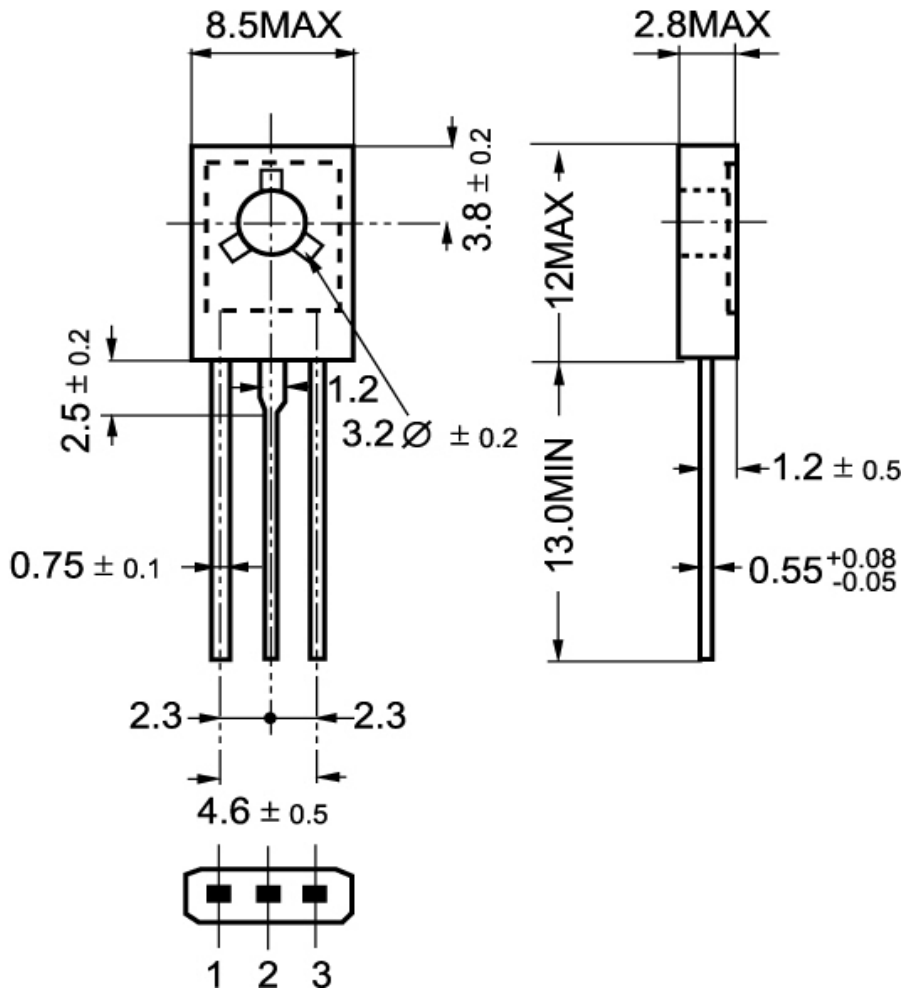


Fig.2 Outline dimensions